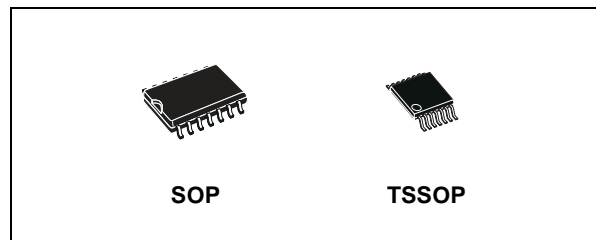




# 74LVXU04

## LOW VOLTAGE CMOS HEX INVERTER (SINGLE STAGE) WITH 5V TOLERANT INPUTS

- HIGH SPEED :  
 $t_{PD} = 5.0ns$  (TYP.) at  $V_{CC} = 3.3V$
- 5V TOLERANT INPUTS
- LOW POWER DISSIPATION:  
 $I_{CC} = 2 \mu A$  (MAX.) at  $T_A = 25^\circ C$
- LOW NOISE:  
 $V_{OLP} = 0.3V$  (TYP.) at  $V_{CC} = 3.3V$
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 4mA$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:  
 $V_{CC}(OPR) = 2V$  to  $3.6V$  (1.2V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 04
- IMPROVED LATCH-UP IMMUNITY
- POWER DOWN PROTECTION ON INPUTS



### ORDER CODES

PACKAGE	TUBE	T & R
SOP	74LVXU04M	74LVXU04MTR
TSSOP		74LVXU04TTR

As the internal circuit is composed of a single stage inverter, it can be used in analog application such as crystal oscillator.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage.

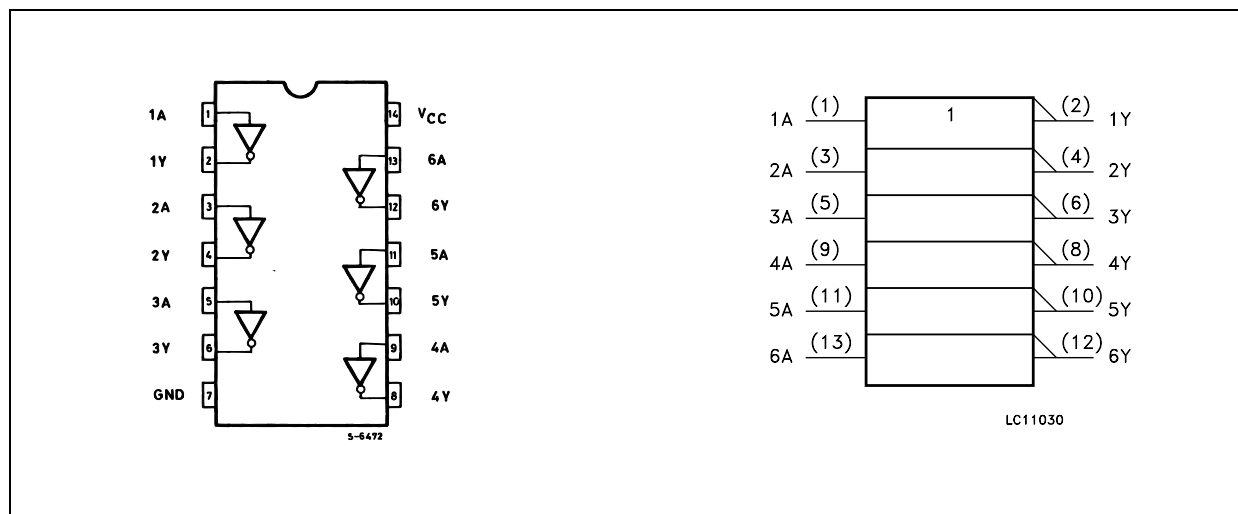
This device can be used to interface 5V to 3V system. It combines high speed performance with the true CMOS low power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

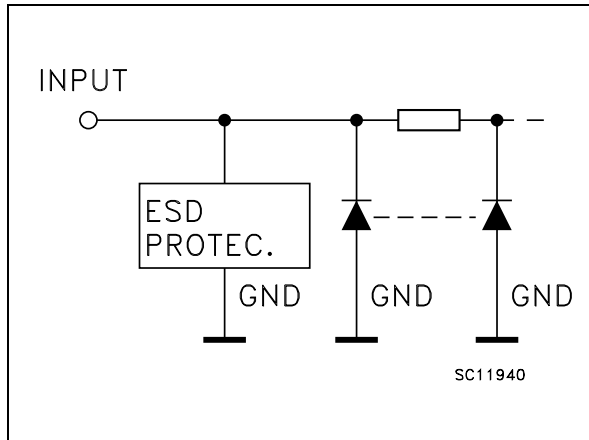
### DESCRIPTION

The 74LVXU04 is a low voltage CMOS HEX INVERTER (SINGLE STAGE) fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology. It is ideal for low power, battery operated and low noise 3.3V applications.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



**INPUT EQUIVALENT CIRCUIT**



**PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

**TRUTH TABLE**

A	Y
L	H
H	L

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage (note 1)	2 to 3.6	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 2) (V <sub>CC</sub> = 3.3V)	0 to 100	ns/V

1) Truth Table guaranteed: 1.2V to 3.6V

2) V<sub>IN</sub> from 0.8V to 2.0V

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	2.0		1.7			1.7		1.7		V
		3.0 to 3.6		0.8			0.8		0.8		
				V <sub>CC</sub>			V <sub>CC</sub>		V <sub>CC</sub>		
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.3		0.3		0.3	V
		3.0 to 3.6				0.2		0.2		0.2	
						V <sub>CC</sub>		V <sub>CC</sub>		V <sub>CC</sub>	
V <sub>OH</sub>	High Level Output Voltage	2.0	I <sub>O</sub> =-50 μA	1.9	2.0		1.9		1.9		V
		3.0	I <sub>O</sub> =-50 μA	2.9	3.0		2.9		2.9		
		3.0	I <sub>O</sub> =-4 mA	2.58			2.48		2.4		
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	
		3.0	I <sub>O</sub> =4 mA			0.36		0.44		0.55	
I <sub>I</sub>	Input Leakage Current	3.6	V <sub>I</sub> = 5V or GND			± 0.1		± 1		± 1	μA
I <sub>CC</sub>	Quiescent Supply Current	3.6	V <sub>I</sub> = V <sub>CC</sub> or GND			2		20		20	μA

## DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>OLP</sub>	Dynamic Low Voltage Quiet Output (note 1, 2)	3.3	C <sub>L</sub> = 50 pF		0.3	0.5					V
V <sub>OLV</sub>				-0.5	-0.3						
V <sub>IHD</sub>	Dynamic High Voltage Input (note 1, 3)	3.3		2							
V <sub>ILD</sub>				Dynamic Low Voltage Input (note 1, 3)	3.3			0.8			

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V<sub>ILD</sub>), 0V to threshold (V<sub>IHD</sub>), f=1MHz.

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r = t_f = 3\text{ns}$ )

Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)	$C_L$ (pF)	$T_A = 25^\circ\text{C}$			$-40$ to $85^\circ\text{C}$		$-55$ to $125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time	2.7	15		6.5	10.4	1.0	13.7	1.0	13.7	ns
		2.7	50		8.5	13.0	1.0	15.2	1.0	15.2	
		3.3 <sup>(*)</sup>	15		5.0	8.9	1.0	10.5	1.0	10.5	
		3.3 <sup>(*)</sup>	50		7.5	11.4	1.0	13.0	1.0	13.0	
$t_{OSLH}$ $t_{OSHL}$	Output To Output Skew Time (note 1, 2)	2.7	50		0.5	1.0		1.5		1.5	ns
		3.3 <sup>(*)</sup>	50		0.5	1.0		1.5		1.5	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW

2) Parameter guaranteed by design

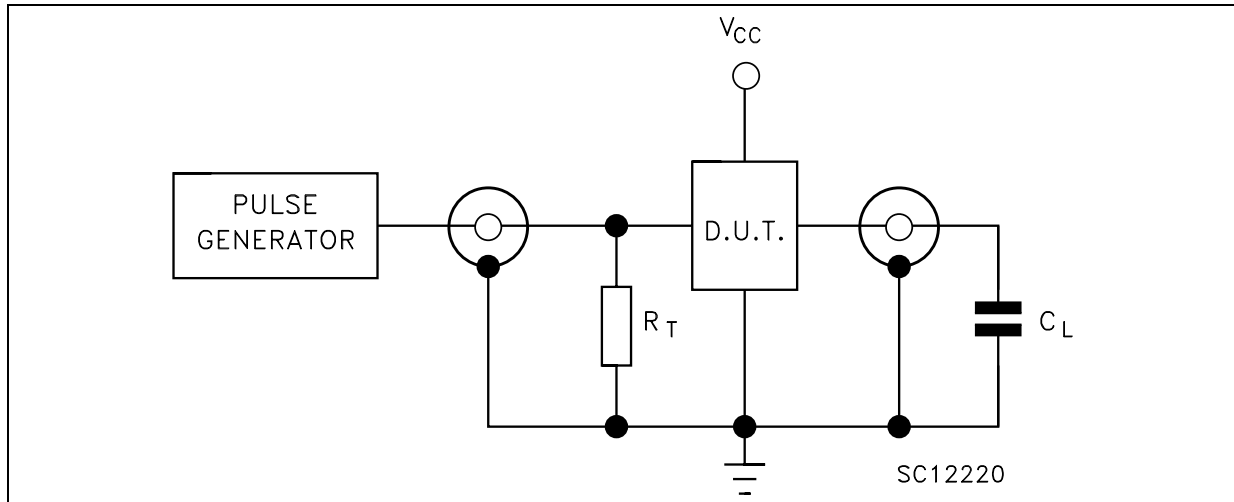
(\*) Voltage range is  $3.3\text{V} \pm 0.3\text{V}$

**CAPACITIVE CHARACTERISTICS**

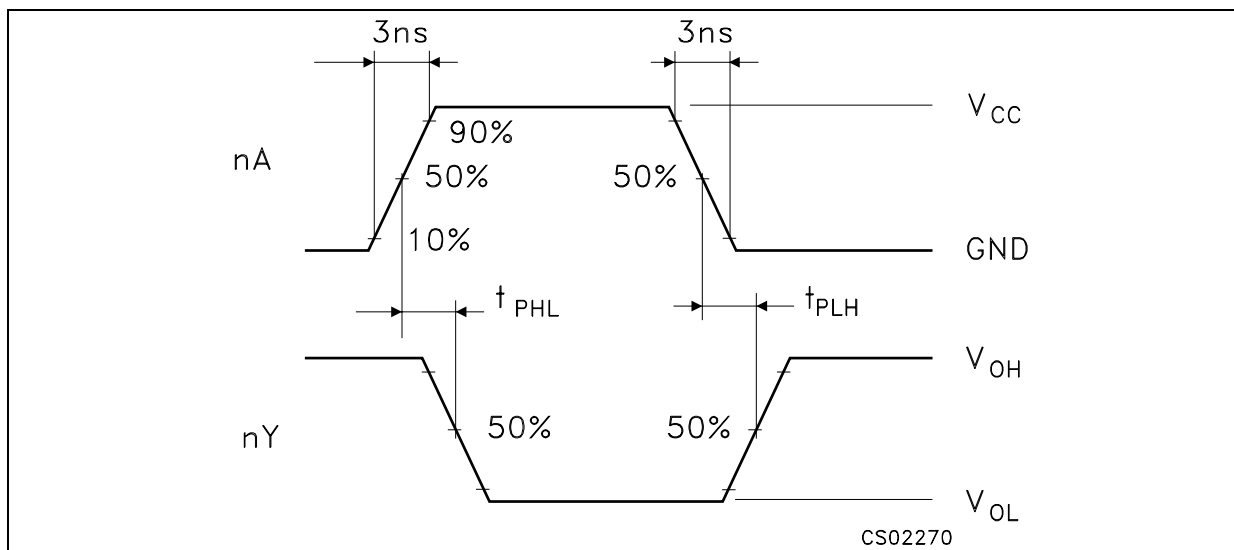
Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ\text{C}$			$-40$ to $85^\circ\text{C}$		$-55$ to $125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$C_{IN}$	Input Capacitance	3.3			5	10		10		10	pF
$C_{PD}$	Power Dissipation Capacitance (note 1)	3.3			9						pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6$  (per gate)

## TEST CIRCUIT

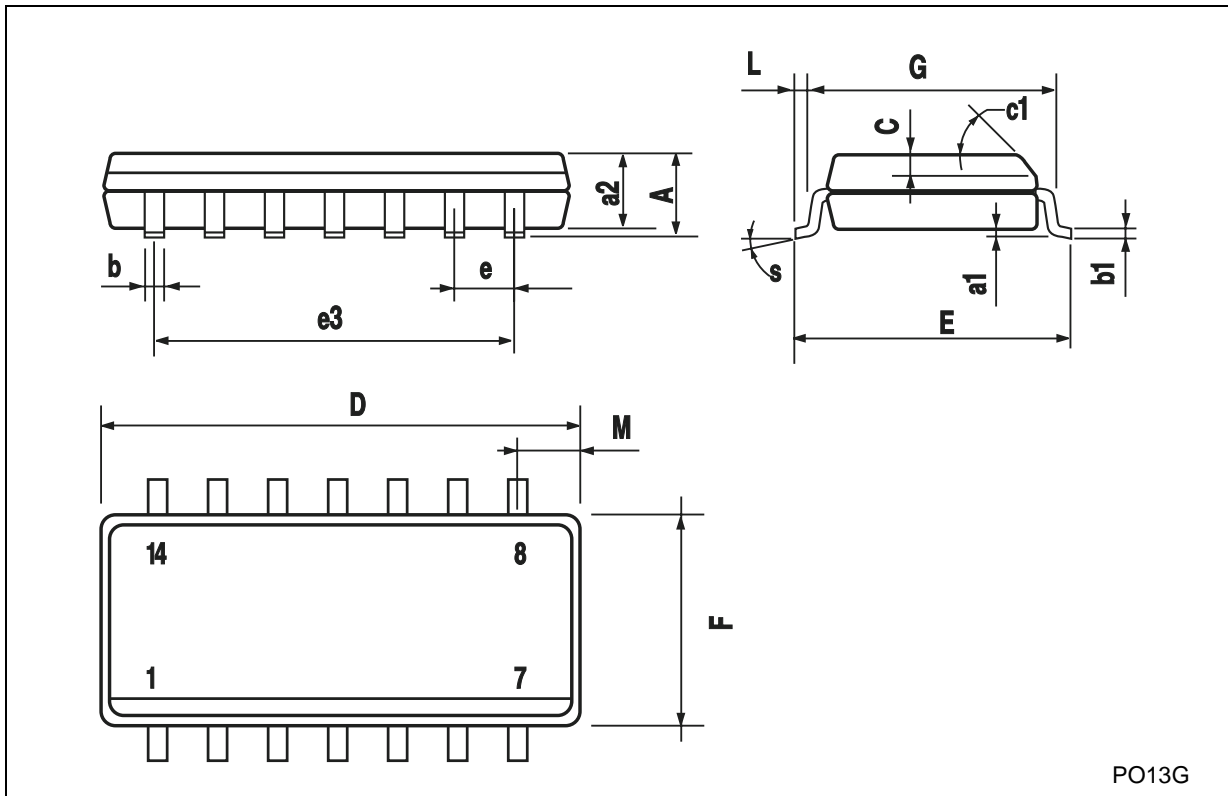


$C_L = 15/50\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

WAVEFORM : PROPAGATION DELAYS ( $f=1\text{MHz}$ ; 50% duty cycle)

**SO-14 MECHANICAL DATA**

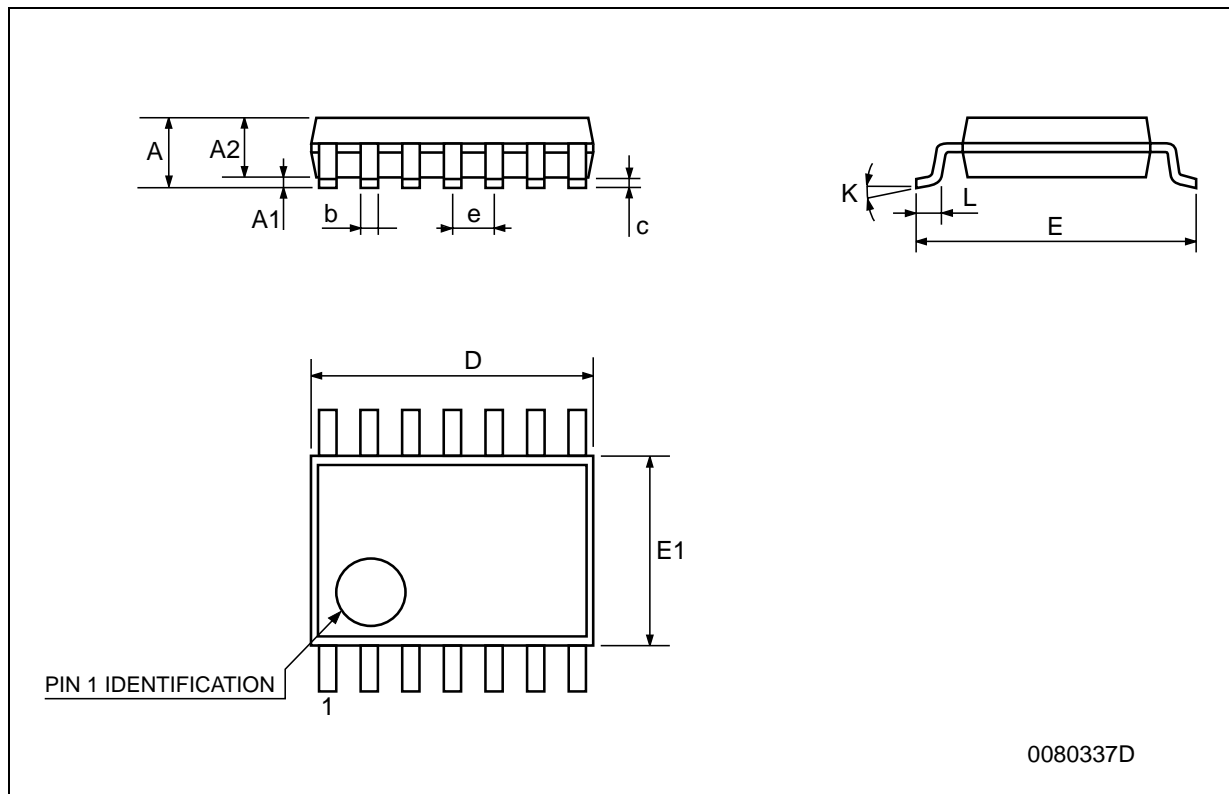
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

## TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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